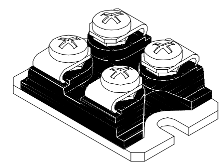
International
IOR Rectifier

I27139- 01/03

FC40SA50FK

HEXFET® Power MOSFET

V_{DSS}	$R_{DS(on)}$ typ.	I_D
500V	**0.084 Ω**	**40A**



SOT-227

Applications
- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

Benefits
- Low Gate Charge Qg results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Low $R_{DS(on)}$
- Fully Insulated Package

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	40	
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	26	A
I_{DM}	Pulsed Drain Current ①	160	
P_D @T_C = 25°C	Power Dissipation	430	W
	Linear Derating Factor	3.45	W/°C
V_{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	9.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	–	1240	mJ
I_{AR}	Avalanche Current①	–	40	A
E_{AR}	Repetitive Avalanche Energy①	–	43	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	–	0.29	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.05	–	

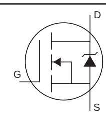
Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	–	–	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–	0.60	–	V/°C	Reference to 25°C, I_D = 1mA⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–	0.084	0.10	Ω	V_{GS} = 10V, I_D = 24A ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	–	5.0	V	V_{DS} = V_{GS}, I_D = 250µA
I_{DSS}	Drain-to-Source Leakage Current	–	–	50	µA	V_{DS} = 500V, V_{GS} = 0V
		–	–	250		V_{DS} = 400V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	–	–	250	nA	V_{GS} = 30V
	Gate-to-Source Reverse Leakage	–	–	-250		V_{GS} = -30V

Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	23	–	–	S	V_{DS} = 50V, I_D = 28A
Q_g	Total Gate Charge	–	–	270	nC	I_D = 40A
Q_{gs}	Gate-to-Source Charge	–	–	84		V_{DS} = 400V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–	–	130		V_{GS} = 10V, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	–	25	–	ns	V_{DD} = 250V
t_r	Rise Time	–	140	–		I_D = 40A
$t_{d(off)}$	Turn-Off Delay Time	–	55	–		R_G = 1.0Ω
t_f	Fall Time	–	74	–		V_{GS} = 10V,See Fig. 10 ④
C_{iss}	Input Capacitance	–	8310	–	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–	960	–		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–	120	–		f = 1.0MHz, See Fig. 5
C_{oss}	Output Capacitance	–	10170	–		V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz
C_{oss}	Output Capacitance	–	240	–		V_{GS} = 0V, V_{DS} = 480V, f = 1.0MHz
C_{oss} eff.	Effective Output Capacitance	–	440	–		V_{GS} = 0V, V_{DS} = 0V to 480V ⑤

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–	–	40	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–	–	160		
V_{SD}	Diode Forward Voltage	–	–	1	V	T_J = 25°C, I_S = 40A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	–	620	940	ns	T_J = 25°C, I_F = 47A
Q_{rr}	Reverse Recovery Charge	–	14	21	µC	di/dt = 100A/µs ④
I_{RRM}	Reverse Recovery Current	–	38	-	A	T_J = 25°C
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)

② Starting T_J = 25°C, L = 1.55mH, R_G = 25Ω, I_{AS} = 40A, dv/dt =5.5V/ns (See Figure 12a)

③ I_{SD} ≤ 40A, di/dt ≤ 150A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

⑤ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}

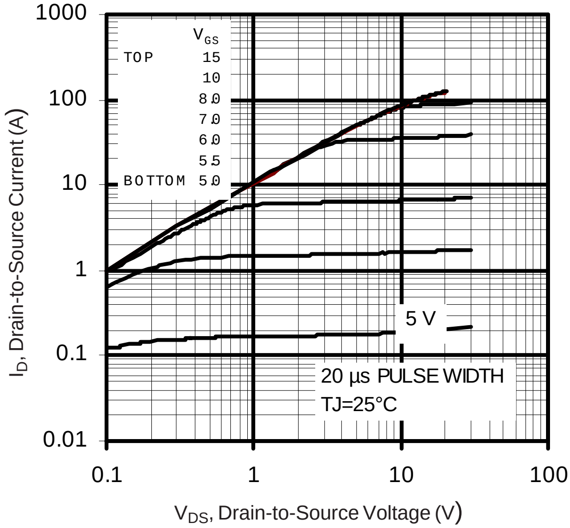


Fig 1. Typical Output Characteristics

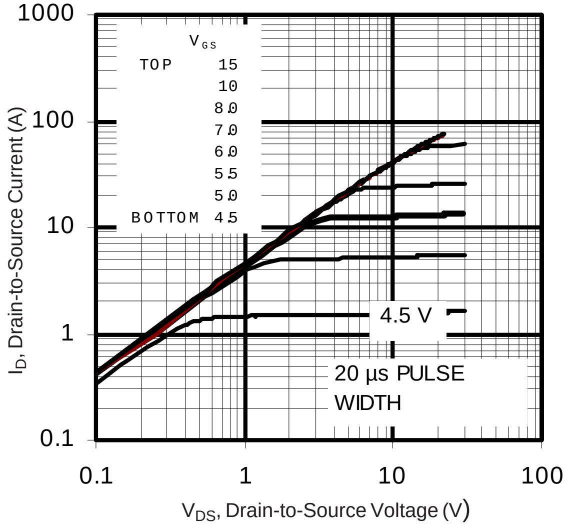


Fig 2. Typical Output Characteristics

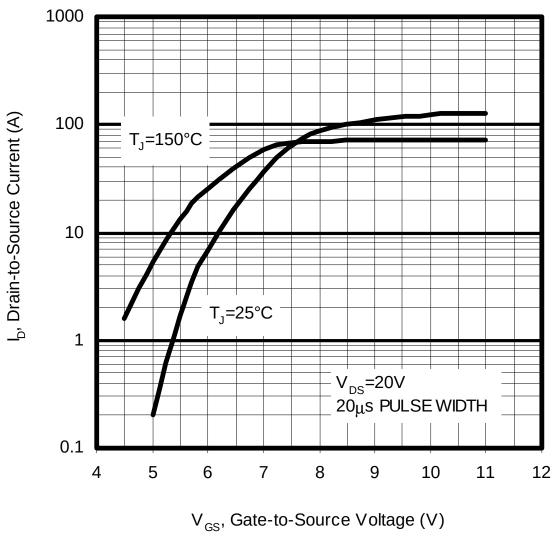


Fig 3. Typical Transfer Characteristics

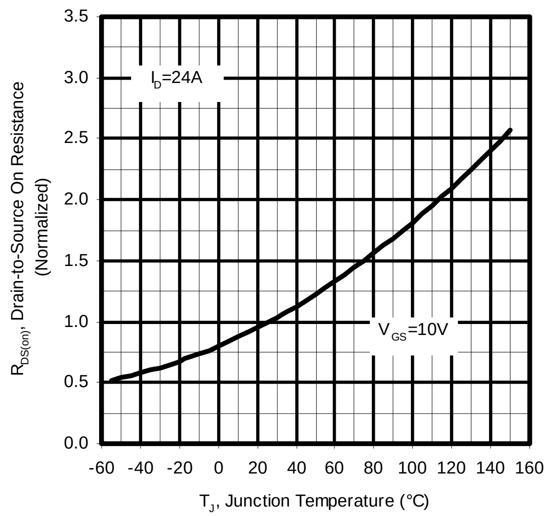


Fig 4. Normalized On-Resistance Vs. Temperature

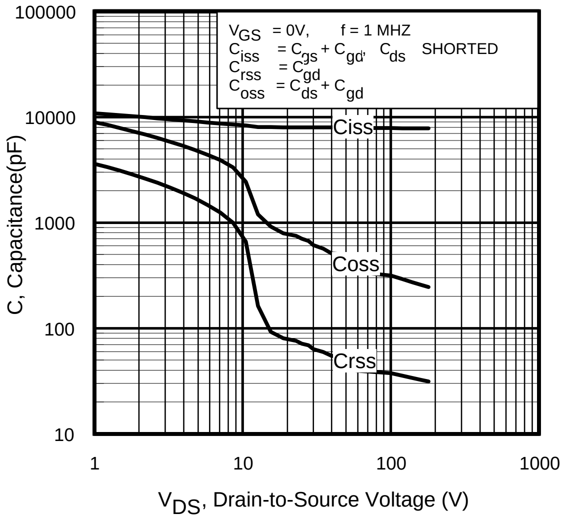


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

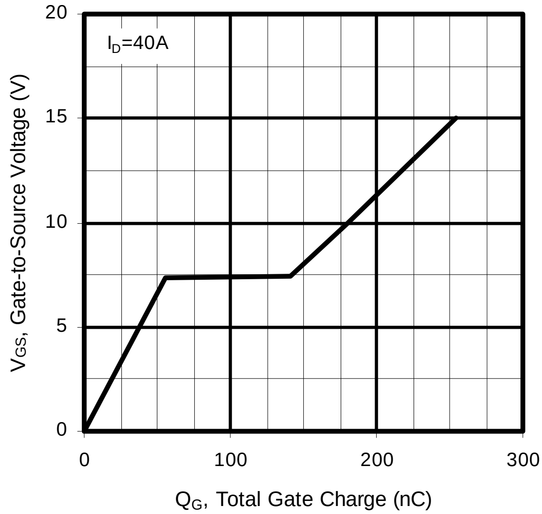


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

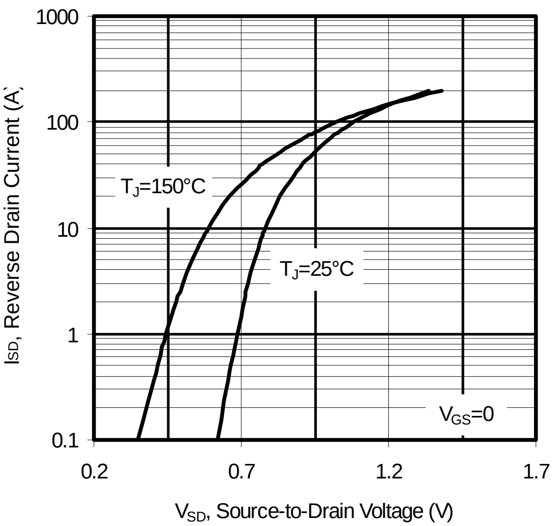


Fig 7. Typical Source-Drain Diode Forward Voltage

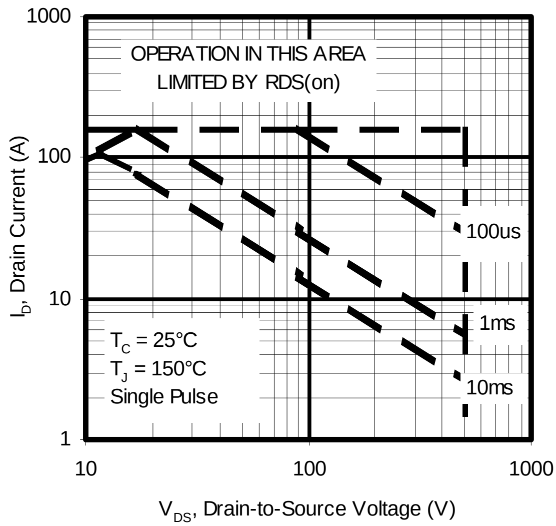


Fig 8. Maximum Safe Operating Area

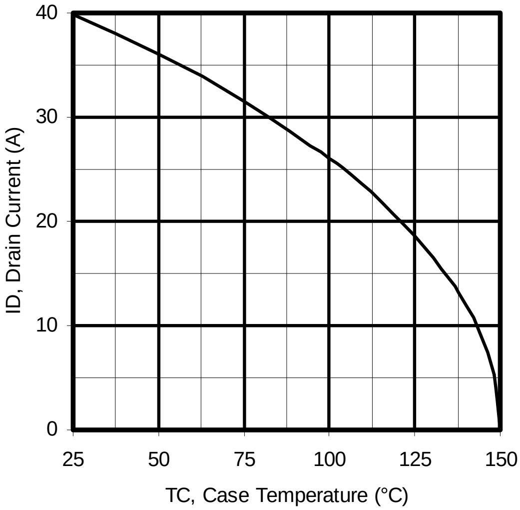


Fig 9. Maximum Drain Current Vs. Case Temperature

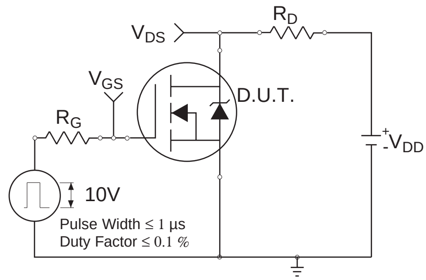


Fig 10a. Switching Time Test Circuit

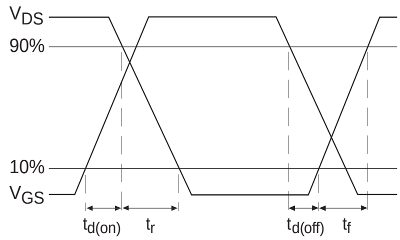
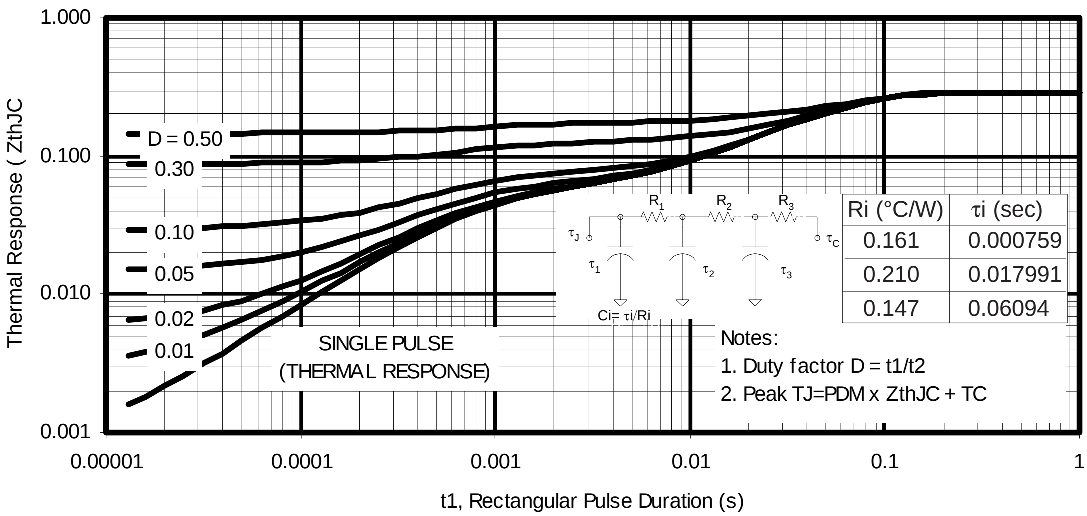


Fig 10b. Switching Time Waveforms



Ri (°C/W)	τi (sec)
0.161	0.000759
0.210	0.017991
0.147	0.06094

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

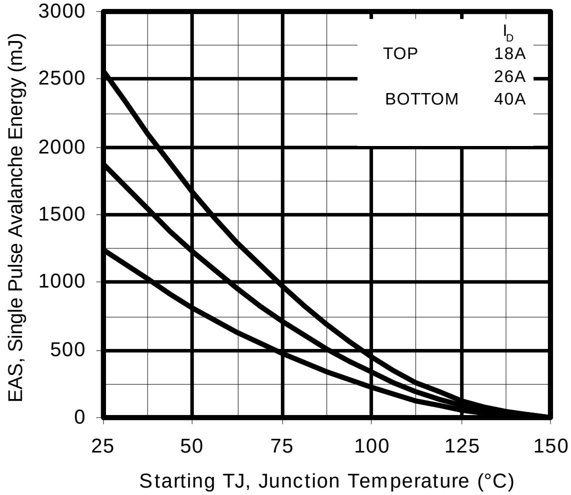


Fig 12a. Maximum Avalanche Energy Vs. Drain Current

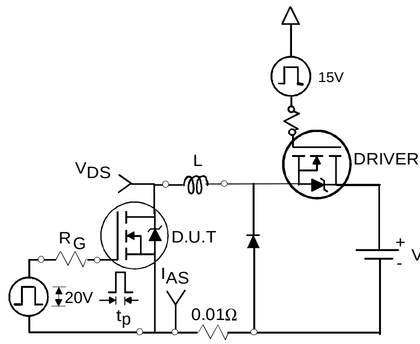


Fig 12c. Unclamped Inductive Test Circuit

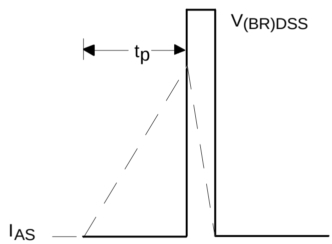


Fig 12d. Unclamped Inductive Waveforms

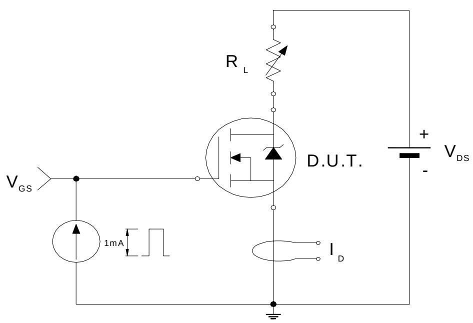


Fig 13a. Gate Charge Test Circuit

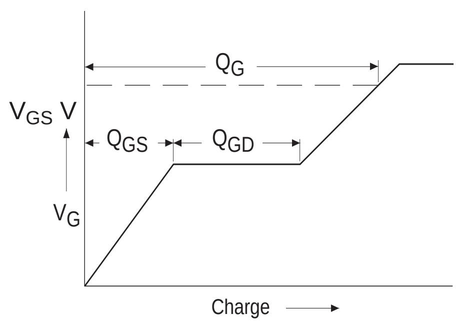
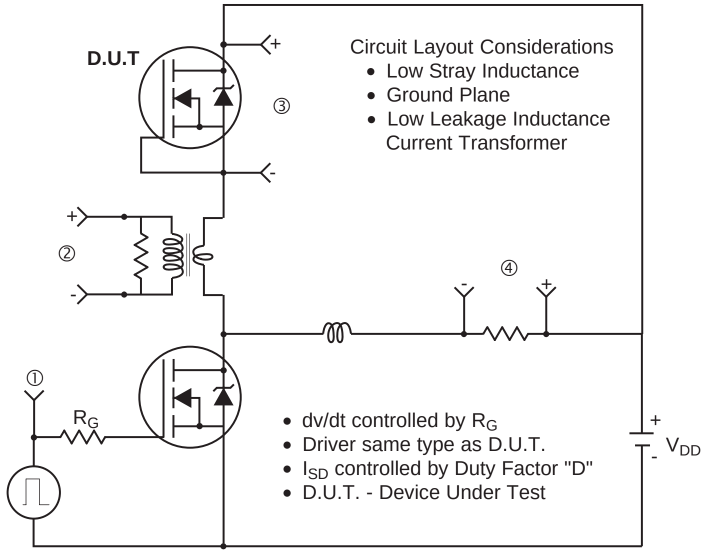
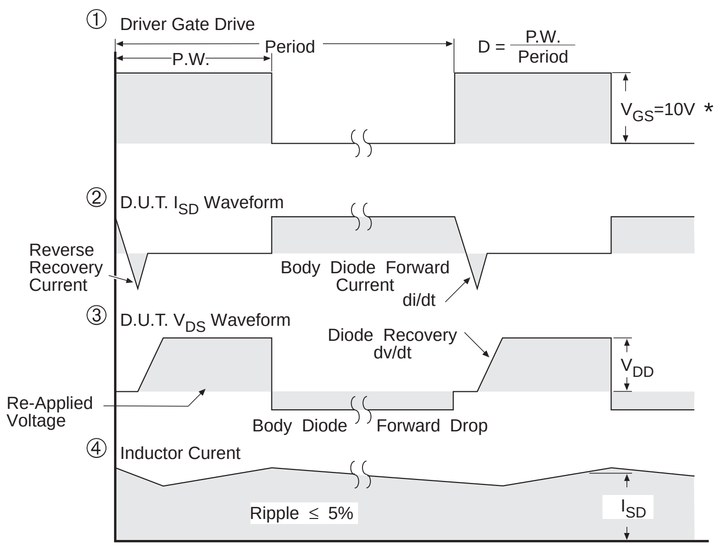


Fig 13b. Basic Gate Charge Waveform

Peak Diode Recovery dv/dt Test Circuit

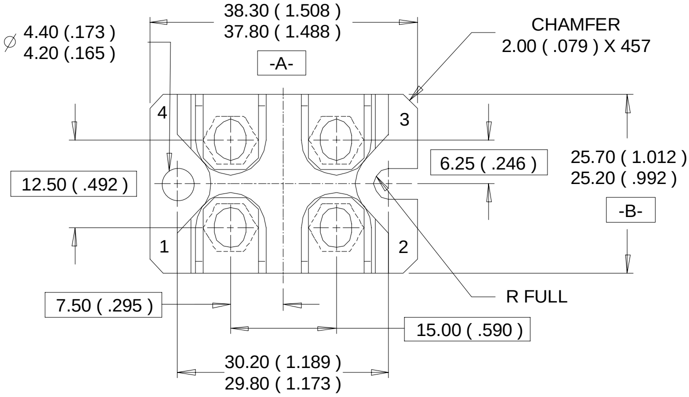


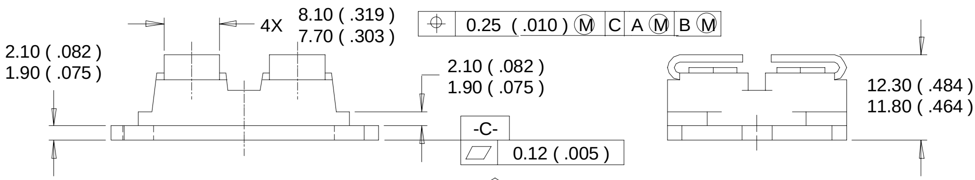


* V_{GS} = 5V for Logic Level Devices

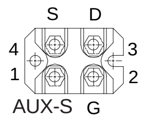
Fig 14. For N-Channel HEXFET® Power MOSFETs

SOT-227 Package Details





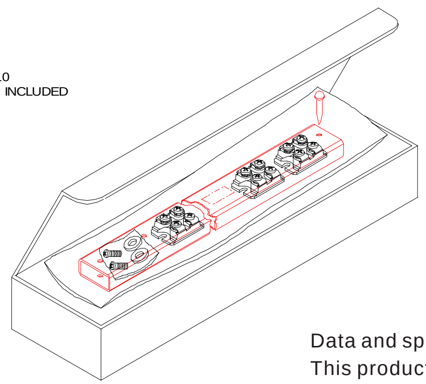
LEAD ASSIGMENTS



HEXFET

Note :
AUX-S is a low current input intended for driving purpose only

QUANTITY PER TUBE IS 10
M4 SREW AND WASHER INCLUDED



Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.

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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
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